COMPARISON TABLE

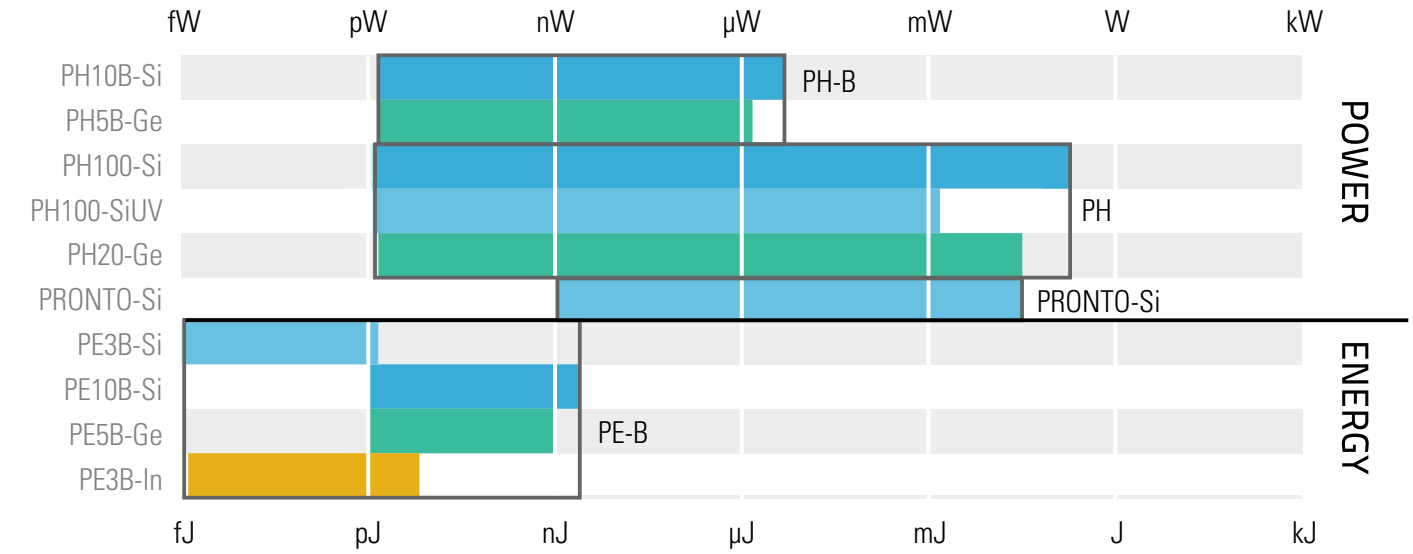
FOR POWER MEASUREMENTS

MODEL	PMAX	NOISE LEVEL	λMIN	λMAX	SENSOR TYPE	APERTURE	SEE PAGE
PH5B-Ge	40 µW	40 pW	800 nm	1.65 µm	Germanium	5 mm Ø	110
PH10B-Si	200 µW	50 pW	210 nm	1.08 µm	UV-Silicon	10 mm Ø	110
PH100-SiUV	4 mW	10 pW	210 nm	1.08 µm	UV-Silicon	10 mm Ø	112
PH100-SiUV-OD.3	11 mW	30 pW	210 nm	1.08 µm	UV-Silicon	10 mm Ø	112
PH100-SiUV-OD1	38 mW	100 pW	400 nm	1.08 µm	UV-Silicon	10 mm Ø	112
PH20-Ge	30 mW	60 pW	800 nm	1.65 µm	Germanium	5 mm Ø	112
PH100-Si-HA	36 mW	10 pW	350 nm	1.08 µm	Silicon	10 mm Ø	112
PH100-Si-HA-OD1	300 mW	100 pW	420 nm	1.08 µm	Silicon	10 mm Ø	112
PH20-Ge-OD1	300 mW	600 pW	900 nm	1.65 µm	Germanium	5 mm Ø	112
PRONTO-Si	300 mW	10 pW	320 nm	1.1 µm	Silicon	10 X 10 mm	116
PH20-Ge-OD2	500 mW	6 nW	950 nm	1.65 µm	Germanium	5 mm Ø	105
PH100-Si-HA-OD2	750 mW	1 nW	630 nm	1.1 µm	Silicon	10 mm Ø	112

FOR ENERGY MEASUREMENTS

MODEL	EMAX	NOISE LEVEL	λMIN	λMAX	SENSOR TYPE	APERTURE	SEE PAGE
PE3B-Si	30 pJ	8 fJ	210 nm	1.08 µm	UV-Silicon	3 mm Ø	114
PE3B-In	300 pJ	30 fJ	900 nm	1.7 µm	InGaAs	3 mm Ø	114
PE5B-Ge	3 nJ	1 pJ	800 nm	1.65 µm	Germanium	5 mm Ø	114
PE10B-Si	150 nJ	1.5 pJ	210 nm	1.08 µm	UV-Silicon	10 mm Ø	114

Available with INTEGRA all-in-one detector + meter



Silicon/UV-Silicon Sensors
190 - 1100 nm

Germanium Sensor
800 - 1650 nm

InGaAs Sensor
900 - 1700 nm

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